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FILE 'REGISTRY' ENTERED AT 14:23:50 ON 01 APR 2009
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FILE 'LCA' ENTERED AT 13:18:18 ON 01 APR 2009

L1 364 SEA (VALVE? OR METAL#### OR NIOBIUM? OR ALOY? OR
AMALGAM? OR INGOT? OR BULLION?) (2A) (PENTOXIDE? OR
OXIDE? OR DIOXIDE? OR SUBOXIDE? OR SUB (2A) OXIDE)

L2 2 SEA GETTER? (2A) (MATERIAL? OR GAS### OR SUBSTANCE?)

L3 2173 SEA HYDROGEN OR 1333-74-0 OR H2 OR NOBLE (2A) GAS

L4 5586 SEA PARTICL? OR MICROPARTICL? OR PARTICULAT? OR DUST? OR
GRIT? OR GRAIN# OR GRANUL? OR POWDER? OR SOOT? OR SMUT?
OR FINES# OR PRILL? OR FLAKE# OR PELLET? OR BB#

L5 13 SEA (OXYGEN? OR O2) (2A) REDUC?

L6 0 SEA B213 OR B (A) 213

L7 79 SEA ASTM#

L8 182 SEA CAPACIT!R? OR CAPACITANC? OR CAPACIT!R (2A) ELECTRODE
?

L9 31 SEA (FLOW OR FLOWS OR FLOWED OR FLOWING#) (2A) (VALUE?
OR PARAMETER? OR NUMBER? OR NUMERICAL? OR THRESHOLD? OR
LIMIT?)

L10 21 SEA (MILLIG? OR MG#) (W) (S OR SECOND# OR SEC#)

L11 153 SEA (FLOW OR FLOWS OR FLOWED OR FLOWING#) (2A) (HIGH? OR
INCREASES? OR ELEVAT? OR HEIGHTEN? OR RAIS? OR AUGMENT? OR
LARGE? OR GREAT?)

FILE 'LREGISTRY' ENTERED AT 13:36:59 ON 01 APR 2009

L12 5 SEA (NB (L) O)/ELS (L) 2/ELC.SUB

FILE 'REGISTRY' ENTERED AT 13:38:21 ON 01 APR 2009

L13 279 SEA (NB (L) O)/ELS (L) 2/ELC.SUB
E NIOBIUM/CN

L14 1 SEA NIOBIUM/CN

FILE 'LCA' ENTERED AT 13:43:17 ON 01 APR 2009

L15 8 SEA GETTERS/IT

L16 19 SEA GRANULATION/IT

FILE 'LREGISTRY' ENTERED AT 13:45:37 ON 01 APR 2009

L17 2 SEA (NB (L) H)/ELS (L) 2/ELC.SUB

FILE 'REGISTRY' ENTERED AT 13:46:49 ON 01 APR 2009

L18 159 SEA (NB (L) H)/ELS (L) 2/ELC.SUB

L19 FILE 'STNGUIDE' ENTERED AT 13:47:35 ON 01 APR 2009
0 SEA GETTER?

L20 FILE 'REGISTRY' ENTERED AT 13:51:07 ON 01 APR 2009
E NIOBIUM OXIDE/CN
2 SEA "NIOBIUM OXIDE"/CN

L21 FILE 'HCA' ENTERED AT 13:52:44 ON 01 APR 2009
20098 SEA L13 OR L20
L22 73115 SEA L14
L23 681 SEA L18
L24 21 SEA L19 AND L21
L25 14 SEA L24 AND (VALV? OR L22 OR L23 OR L8 OR L4 OR L5 OR
L3)

L26 FILE 'REGISTRY' ENTERED AT 14:01:57 ON 01 APR 2009
E HYDROGEN/CN
1 SEA HYDROGEN/CN

L27 FILE 'HCA' ENTERED AT 14:02:13 ON 01 APR 2009
356645 SEA L26
L28 7 SEA L24 AND L27

L29 FILE 'HCA' ENTERED AT 14:04:05 ON 01 APR 2009
180 SEA L19 AND VALV?
L30 2 SEA L29 AND L21
L31 11 SEA L29 AND L22
L32 1 SEA L29 AND L23
L33 23 SEA L25 OR L28 OR L30 OR L32 OR L31
L34 7 SEA L24 NOT L33
L35 349 SEA L8 AND (L9 OR L10 OR L11)
L36 74 SEA L8 AND L9
L37 13 SEA L8 AND L10
L38 269 SEA L8 AND L11
L39 7 SEA L36 AND L38
L40 0 SEA L8 AND L6
L41 63 SEA L8 AND L7
L42 0 SEA L41 AND (L9 OR L10 OR L11)
L43 0 SEA L6 AND (L9 OR L10 OR L11)
L44 203 SEA B213 OR B (A) 213
L45 1 SEA L44 AND L7

L46 FILE 'HCA' ENTERED AT 14:18:20 ON 01 APR 2009
0 SEA L41 AND L36
L47 0 SEA L41 AND L38
L48 0 SEA L21 AND L36
L49 2 SEA L21 AND L38

L50 0 SEA L21 AND L41
L51 23 SEA L37 OR L39 OR L45 OR L49
L52 20 SEA 1808-2003/PY,PRY,AY AND L33
L53 6 SEA 1808-2003/PY,PRY,AY AND L34
L54 18 SEA 1808-2003/PY,PRY,AY AND L51

=> FIL HCA

FILE 'HCA' ENTERED AT 14:24:00 ON 01 APR 2009
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(SEARCH OF REQUEST'S "ADDITIONAL COMMENTS")

=> D L54 1-18 BIB ABS HITRN HITIND RE

L54 ANSWER 1 OF 18 HCA COPYRIGHT 2009 ACS on STN
AN 136:13484 HCA Full-text
TI SiO₂ films deposited on silicon at low temperature by
plasma-enhanced decomposition of hexamethyldisilazane: Defect
characterization
AU Croci, S.; Pecqueur, A.; Autran, J. L.; Vedda, A.; Caccavale, F.;
Martini, M.; Spinolo, G.
CS Laboratoire de Physique de la Matière, UMR CNRS 5511, Institut
National des Sciences Appliquées de Lyon, Villeurbanne, F-69621, Fr.
SO Journal of Vacuum Science & Technology, A: Vacuum, Surfaces, and
Films (2001), 19(5), 2670-2675
CODEN: JVTAD6; ISSN: 0734-2101
PB American Institute of Physics
DT Journal
LA English
AB Silicon dioxide films have been deposited by plasma-enhanced chem.
vapor deposition at low substrate temp. (50°C) in a parallel-plate
reactor using hexamethyldisilazane (HMDS), dild. in He, and O₂ as Si
and O precursors. The effect of the O₂/(HMDS+He) flow rate ratio on
the oxide properties has been investigated in the range of 0.05-1.25
by means of deposition rate, wet etching rate, secondary ion mass
spectrometry, thermally stimulated luminescence, and high frequency
capacitance-voltage measurements. Both the deposition rate and the
etching rate increase by increasing the O₂/(HMDS+He) flow rate ratio
and reach a const. value at flow rate ratios higher than 0.6. The
strong increase and satn. in the deposition rate can be attributed to